

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended. Claims 1, 8 - 14 and 18 - 23 have been canceled without prejudice or disclaimer and the subject matter thereof directed to non-elected species has been presented in a divisional application.

1. (Canceled)

2. (Currently Amended) A method ~~as recited in claim 1~~ A method of protecting a material surface comprising steps of

depositing a material layer on said material surface, said material layer providing a chemical reaction interface at a surface of said material layer,
lithographically patterning said material layer, and
removing said material layer from said material surface selectively to said material surface, wherein said material layer provides a chemical reaction interface and is formed of a low density and high permeability material relative to other semiconductor materials and wherein said depositing step includes

converting said material layer using a plasma containing hydrogen and oxygen or water vapor.

3. (Original) A method as recited in claim 2, wherein said removing step includes

etching said material layer with a mixture of hydrogen fluoride and a hygroscopic material at a chemical reaction interface.

4. (Original) A method as recited in claim 3, wherein said low density and high permeability material is a tunable etch-resistant anti-reflective coating (TERA) material.

5. (Original) A method as recited in claim 3, wherein said hygroscopic material is an organic solvent or an inorganic acid.

6. (Original) A method as recited in claim 5, wherein said organic solvent is ethylene glycol.

7. (Original) A method as recited in claim 5, wherein said inorganic acid is sulfuric acid.

8. - 14. (Canceled)

15. (Previously Presented) A mask structure for semiconductor device manufacture comprising a layer of material providing a chemical reaction interface at a surface of said layer of material, wherein said chemical reaction interface provides enhanced selectivity of an etching process for removal of said layer of material.

16. (Original) A mask structure as recited in claim 15, wherein said layer of material has OH⁻ groups or water incorporated therein.

17. (Previously Presented) A mask structure as recited in claim 16, wherein said layer of material is a tunable, etch-resistant anti-reflective coating material.

18. - 23 (Canceled)

24. (Previously Presented) A mask structure as recited in claim 15, wherein said layer of material includes hydrated or oxidized tunable etch-resistant anti-reflective coating (TERA) material or graded TERA material.